

SPECIFICATION OF LED CHIP C630-55NN [RED]

1) Commodity Type and Physical Characteristics.

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|----------------------|--------------|------------------|------------------------|
| 1. Material | InGaAlP/GaAs | | |
| 2. Electrode | Top Side | P (anode) side | :Au Alloy/Al or Au Pad |
| | Bottom Side | N (cathode) side | :Au Alloy |
| 3. Electrode Pattern | Fig.1 | | |
| 4. Chip Size | Fig.2 | | |
| 5. Chip Thickness | Fig.2 | | |
| 6. Emission Area | Fig.2 | | |

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Type	Max.	Unit
Forward Voltage	Vf	If=20mA		1.8	2.1	V
Forward Voltage	Vfp	I _{fp} =500mA		3.00	4.50	V
Reverse Current	I _r	V _r =5V			10	uA
Brightness	I _v	If=20mA	70	120		mcd
Power Intensity	P _o	If=20mA	0.8	1.4		mW
Peak Wavelength	λ _P	If=20mA	625	635	645	nm
Spectral Bandwidth	Δλ	If=20mA		15		nm
Rise Time	t _r	If=20mA		100		ns
Fall Time	t _f	If=20mA		100		ns

‡ Pulse Forward Current condition: Duty=1% and Pulse Width=1us.

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

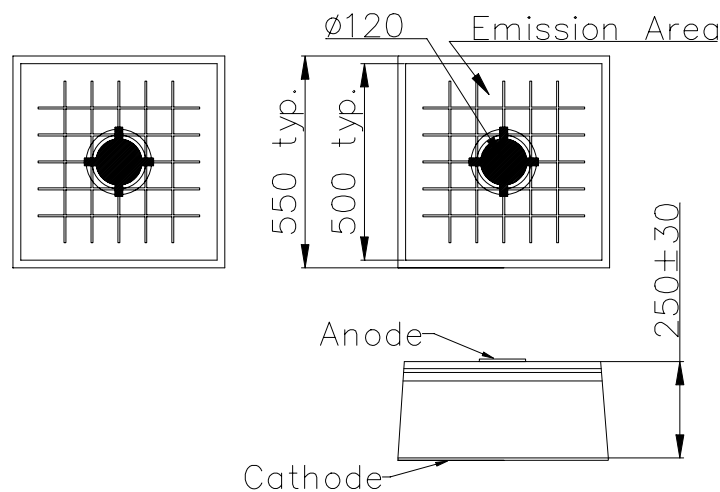


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area